

# **GaN-based Heterostructure Field-effect Transistors And MMICs For High Frequency Applications (Berichte Aus Der Hochfrequenztechnik) By Sanghyun Seo**

**By Sanghyun Seo**

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A heterojunction field effect transistor realizing a high performance by Gallium nitride-based HFET and a method of Service - About Google Patents

<http://www.google.com/patents/US6064082>

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AlGaN/GaN Heterostructure Field-Effect Transistors on Single-Crystal Bulk AlN X. Hu J. Deng density in GaN-based heterostructure field-effect transistors

[http://scholarcommons.sc.edu/cgi/viewcontent.cgi?article=1074&context=elct\\_facpub](http://scholarcommons.sc.edu/cgi/viewcontent.cgi?article=1074&context=elct_facpub)

We report on high electric field stress measurements at room temperature on InAlN/AlN/GaN heterostructure field effect transistor structures. The degradation rate as

<http://scitation.aip.org/content/aip/journal/apl/95/22/10.1063/1.3271183>

The results obtained demonstrate the suitability of GaN-based heterostructure field-effect transistors semiconductor heterostructure field-effect

<http://scitation.aip.org/content/aip/journal/apl/87/14/10.1063/1.2058206>

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of GaN-based Heterostructure Field Effect Transistors (HFETs) effect transistor based on an AlGaN/GaN layer structure for the first time. A two-dimensional

<http://darwin.bth.rwth-aachen.de/opus3/volltexte/2011/3487/pdf/3487.pdf>

Polarization in GaN Based Heterostructures and Heterojunction Field Effect Transistors (HFETs)

[http://link.springer.com/chapter/10.1007/978-0-387-68319-5\\_8](http://link.springer.com/chapter/10.1007/978-0-387-68319-5_8)

Doping design of GaN-based heterostructure field-effect transistors with high electron density for high-power applications

<http://onlinelibrary.wiley.com/doi/10.1002/pssa.200303468/citedby>

DC Characteristics of AlGaN/GaN Heterostructure Field-Effect Transistors on performance of GaN-based photonic devices when grown on bulk GaN. 2003 The

<http://esl.ecsdl.org/lookup/doi/10.1149/1.1626992>

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the regrowth of AlGaN/GaN heterostructure field-effect transistors on N Wide band gap semiconductors such as GaN-based materials have recently become an

<http://m.iopscience.iop.org/0268-1242/28/8/085006/article>

Gallium Nitride-based Microwave High-Power Heterostructure Field-Effect Transistors design, technology, and characterization PROEFSCHRIFT ter verkrijging van de graad

<http://alexandria.tue.nl/extra2/200611998.pdf>

GaN-based heterostructure field effect transistors with ternary and quaternary InAl(Ga)N barrier layers = GaN-basierte Heterostruktur-Feldeffekt-Transistoren mit

<http://publications.rwth-aachen.de/record/231027>

AlGaN/GaN Metal Oxide Semiconductor Heterostructure Field-Effect Transistor Based on a GaN-based metal insulator eld-effect transistors (MISFETs)

[http://iopscience.iop.org/1347-4065/41/7A/L748/pdf/1347-4065\\_41\\_7A\\_L748.pdf](http://iopscience.iop.org/1347-4065/41/7A/L748/pdf/1347-4065_41_7A_L748.pdf)

Abstract. GaN-based electronic devices have established their niches for both high power switching application and high frequency operation due to

<http://ma.ecsdl.org/content/MA2015-01/23/1457.abstract>

Several groups have demonstrated AlGaN/GaN based heterostructure field-effect transistors (HFETs) with record high saturation current in excess of 2 A/mm and RF

<http://ieeexplore.ieee.org/articleDetails.jsp?arnumber=1029491>

Das Buch Sanghyun Seo - GaN-based Heterostructure Field-Effect Transistors and MMICs for High Frequency Applications Berichte aus der Hochfrequenztechnik

<http://www.shaker.de/de/content/catalogue/index.asp?ID=13&ISBN=978-3-8322-8282-0>

GaN-based field effect transistors might replace other compound semiconductor FETs in microwave and, possibly, even in millimeter and submillimeter wave applications.

[http://ieeexplore.ieee.org/xpls/abs\\_all.jsp?arnumber=1531788](http://ieeexplore.ieee.org/xpls/abs_all.jsp?arnumber=1531788)

High electron mobility transistors based on a GaN drain and source resistance in deep-submicron GaN Heterostructure Field Effect Transistors

<http://citeseerx.ist.psu.edu/showciting?cid=4831185>

Nitride Based Insulated Gate Field Effect Transistors M. S. Shur Broadband Center, ECSE and Physics, Computer, and Systems Engineering, Rensselaer Polytechnic

<http://www.ecse.rpi.edu/homepages/shur/Nitride%20Based%20Insulated%20Gate%20Field%20Effect%20Transistors.pdf>

Deep Submicron GaN-based Heterostructure Field Effect Transistors with InGaN Channel and InGaN Back-barrier Designs

<http://citeseerx.ist.psu.edu/viewdoc/summary?doi=10.1.1.531.8691>

Polarization-Engineered Ga-Face GaN-Based Heterostructures for Normally-Off Heterostructure Field-Effect Transistors HYEONGNAM KIM,1 DIGBIJOY NATH,1 SIDDHARTH RAJAN,1,4

<http://link.springer.com/content/pdf/10.1007/s11664-012-2109-3.pdf>

Microwave GaN based Field Effect Transistors Michael S. Shur heterostructure design that has many advantages over more conventional heterostructure FETs.

<http://www.ecse.rpi.edu/homepages/shur/MicrowaveGaNMTTAbstract.pdf>

Hot-Phonon Effect on the Reliability of GaN-Based Heterostructure Field-Effect Transistors Cemil Kayis\* ASELSAN, Inc., Yenimahalle, Ankara/Turkey, +90 312 592 6519

<http://www.csmantech.org/Digests/2015/abstracts/19R-Hot-Phonon%20Effect%20on%20the%20Reliability%20of%20GaN-Based%20Heterostructure%20Field-Effect%20Transistors.pdf>

Special Section on Heterostructure Microelectronics with TWHM 2009: pp.1211-1211 FOREWORD  
Open Access Paper FOREWORD pp.1225-1233 PAPER-GaN-based Devices

<http://search.ieice.org/bin/index.php?vol=E93-C&num=8&lang=E&abst=>

GaN/SiC heterostructure field-effect transistor model contributing to the outstanding performance of GaN/SiC based HFETs is the ability to achieve two dimensional

[http://academicjournals.org/article/article1380812798\\_Rokn-Abadi.pdf](http://academicjournals.org/article/article1380812798_Rokn-Abadi.pdf)

The authors report a 0.2  $\mu\text{m}$  gate GaN/AlGaN heterostructure field effect transistor which operates as a visible blind photodetector with responsivities as high as

[http://digital-library.theiet.org/content/journals/10.1049/el\\_19950247](http://digital-library.theiet.org/content/journals/10.1049/el_19950247)

Maximum Current in Nitride-Based Heterostructure Field-Effect Polarization fields determination in AlGaN/GaN heterostructure field-effect transistors from

[http://scholarcommons.sc.edu/cgi/viewcontent.cgi?article=1083&context=elct\\_facpub](http://scholarcommons.sc.edu/cgi/viewcontent.cgi?article=1083&context=elct_facpub)

1. Introduction. GaN based heterostructure devices are very promising for high-power and high-frequency devices . That is, wide band gap semiconductors such as GaN

<http://www.sciencedirect.com/science/article/pii/S0038110102004197>

GaN-based heterostructure field-effect The excessive gate leakage current of the planar- and mesa-type InAlN/GaN heterostructure field-effect transistors

<http://www.sciencedirect.com/science/article/pii/S0026271412000388>

Investigations of low-frequency noise of GaN-based heterostructure field-effect transistors

[http://digital-library.theiet.org/content/journals/10.1049/el\\_20030548](http://digital-library.theiet.org/content/journals/10.1049/el_20030548)

Heterostructure field effect transistors based on nitride interfaces 3515 wz AlN wz GaN zb AlN zb GaN zb GaN wz GaN E E v c Gap [eV] 0 2 4 0001 111 111/0001

<http://iopscience.iop.org/0953-8984/14/13/309/pdf/c21309.pdf>

The book Sanghyun Seo - GaN-based Heterostructure Field-Effect Transistors and MMICs for High Frequency Applications (ISBN: 978-3-8322-8282-0) was published by Shaker

<http://www.shaker.eu/en/content/catalogue/index.asp?ID=13&ISBN=978-3-8322-8282-0>

Gallium Nitride (GaN) based semiconductor devices have been intensively investigated over the last years due to their inherent material properties; high breakdown

<http://nanotrend.net/research-2/heterostructure-field-effect-transistors/>